

**Features**

- Excellent dynamic characteristics
- Fast turn-on and high di/dt
- Low switching losses

**Typical Applications**

- Design for inverter supply application

品名 : FH1494TN

**I<sub>T(AV)</sub> 1494A****V<sub>DRM</sub> 1200V~2000V****V<sub>RRM</sub> 1000V~1800V****t<sub>q</sub> 15~55μs**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled,	125			1494	A
						1243	
V <sub>DRM</sub>	Repetitive peak off-state voltage	tp=10ms	125	1200		2000	V
				1000		1800	
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak current	at V <sub>DRM</sub> at V <sub>RRM</sub>	125			80	mA
						17	
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave V <sub>R</sub> =0.6V <sub>RRM</sub>	125			17	kA
						1445	
V <sub>TO</sub>	Threshold voltage		125			1.57	V
						0.21	
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =3000A, F=24kN	25	15μs≤t <sub>q</sub> ≤28μs		2.50	V
				29μs≤t <sub>q</sub> ≤55μs		2.10	
dV/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 67%V <sub>DRM</sub> to 1600A, Gate pulse t <sub>r</sub> ≤0.5μs I <sub>GM</sub> =1.5A	125			1500	A/μs
Q <sub>rr</sub>	Recovery charge	I <sub>TM</sub> =1000A, tp=4000μs, di/dt=-20A/μs, V <sub>R</sub> =100V	125		750		μC
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =1000A, tp=4000μs, V <sub>R</sub> =100V dv/dt=30V/μs, di/dt=-20A/μs	125	15		55	μs
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25	40		300	mA
V <sub>GT</sub>	Gate trigger voltage			0.9		3.0	V
I <sub>H</sub>	Holding current			20		500	mA
I <sub>L</sub>	Latching current					1000	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			0.3	V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	DC double side cooled				0.020	°C /W
						0.005	
F <sub>m</sub>	Mounting force			19		26	kN
T <sub>vj</sub>	Junction temperature			-40		125	°C
T <sub>stg</sub>	Stored temperature			-40		140	°C
W <sub>t</sub>	Weight				440		g
Outline		P11					

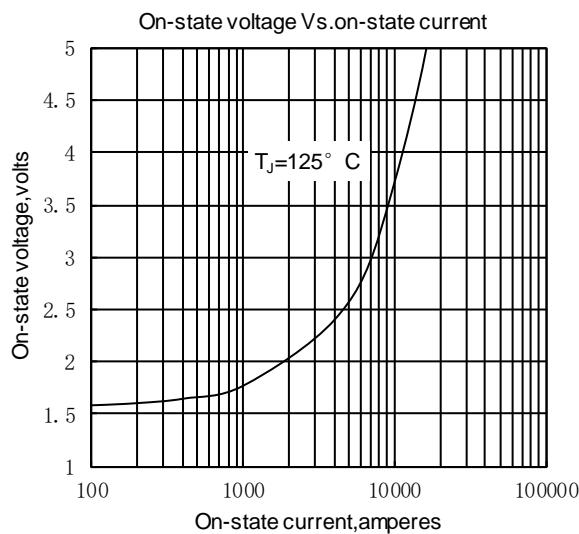


Fig.1

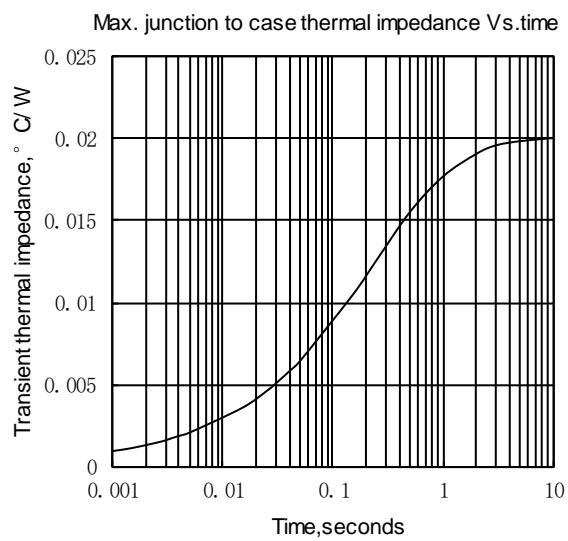


Fig.2

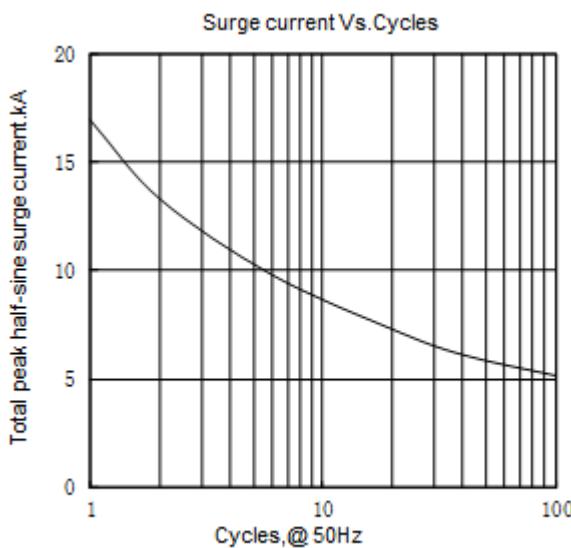


Fig.3

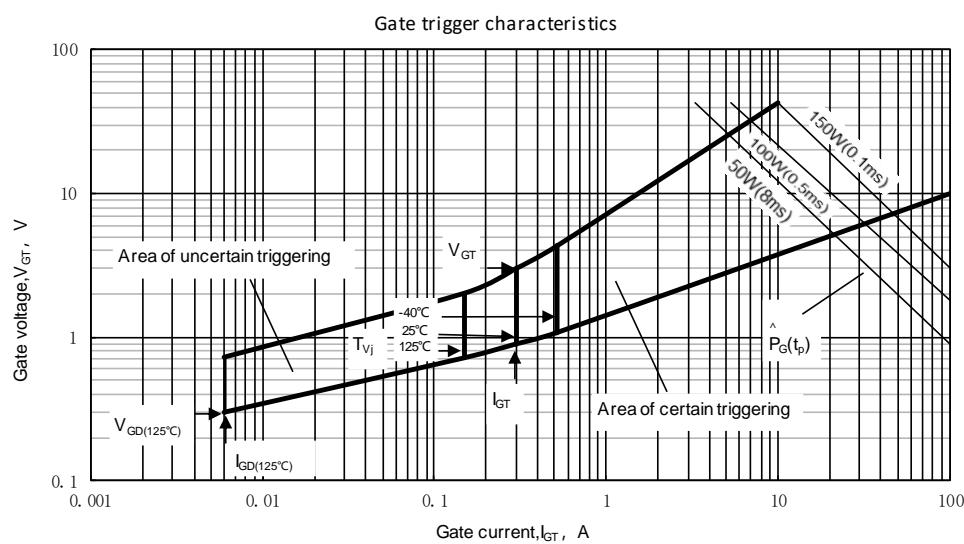


Fig.4

